

# isc P-Channel MOSFET Transistor

### RD3H045SP

### FEATURES

- Drain Current –I\_D= -4.5A@ T\_C=25 $^\circ\!\!\mathbb{C}$
- Drain Source Voltage-: V<sub>DSS</sub>= -45V(Min)
- Static Drain-Source On-Resistance
- :  $R_{DS(on)}$  = 155m  $\Omega$  (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRIPTION

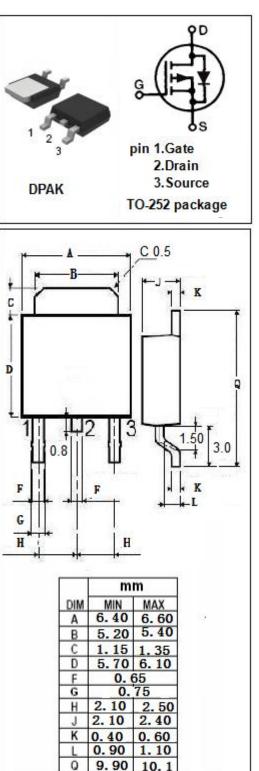
• Designed for use in switch mode power supplies and general purpose applications.

| ABSOLUTE MAXIMUM RATINGS(Ta=25 C) |  |         |      |  |  |  |
|-----------------------------------|--|---------|------|--|--|--|
| SYMBOL                            | PARAMETER VALUE                            |         | UNIT |  |  |  |
| V <sub>DSS</sub>                  | Drain-Source Voltage                       |         | V    |  |  |  |
| $V_{GS}$                          | Gate-Source Voltage-Continuous ±20         |         | V    |  |  |  |
| ID                                | Drain Current-Continuous                   | -4.5    | А    |  |  |  |
| I <sub>DM</sub>                   | Drain Current-Single Pluse                 | -9      | A    |  |  |  |
| PD                                | Total Dissipation @T <sub>c</sub> =25°C 15 |         | W    |  |  |  |
| TJ                                | Max. Operating Junction Temperature        | 150     | °C   |  |  |  |
| T <sub>stg</sub>                  | Storage Temperature                        | -55~150 | °C   |  |  |  |

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

## THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                            | MAX  | UNIT |
|---------------------|--------------------------------------|------|------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case | 8.33 | °C/W |





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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS  | MIN | МАХ  | UNIT               |
|----------------------|---------------------------------|---|-----|------|--------------------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = -1mA                | -45 |      | V                  |
| V <sub>GS</sub> (th) | Gate Threshold Voltage          | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = -1mA | -1  | -3   | V                  |
| $R_{\text{DS(on)}}$  | Drain-Source On-Resistance      | V <sub>GS</sub> = -10V; I <sub>D</sub> = -4.5A            |     | 155  | $\mathbf{m}\Omega$ |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0                |     | ±10  | uA                 |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = -45V; V <sub>GS</sub> = 0               |     | -1   | μA                 |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> = -4.5A; V <sub>GS</sub> = 0               |     | -1.2 | V                  |

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